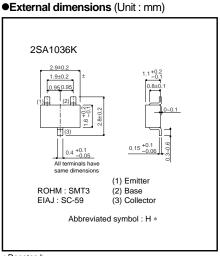
# Medium Power Transistor 2SA1036K

#### Features

- 1) Large I<sub>C</sub>.
- $I_{CMAX.} = -500 \text{mA}$
- 2) Low V<sub>CE(sat)</sub>. Ideal for low-voltage operation.
- 3) Complements the 2SC2411K.

#### Structure

Epitaxial planer type PNP silicon transistor



\* Denotes hre

#### •Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V <sub>CBO</sub>	-40	V	
Collector-emitter voltage	V <sub>CEO</sub>	-32	V	
Emitter-base voltage	V <sub>EBO</sub>	-5	V	
Collector current	lc	-0.5	A *	
Collector power dissipation	Pc	0.2	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

\*Pc MAX. must not be exceeded.

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#### Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-40	-	-	V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage	BVCEO	-32	-	-	V	Ic=-1mA
Emitter-base breakdown voltage	BVEBO	-5	-	-	V	I <sub>E</sub> = -100μA
Collector outoff current	Ісво	-	-	-1	μA	V <sub>CB</sub> = -20V
Emitter cutoff current	I <sub>EBO</sub>	-	-	-1	μΑ	$V_{EB} = -4V$
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.6	V	I <sub>C</sub> /I <sub>B</sub> = -300mA/-30mA
DC current transfer ratio	h <sub>FE</sub>	82	-	390	-	V <sub>CE</sub> = -3V, I <sub>C</sub> = -100mA
Transition frequency	f⊤	-	200	-	MHz	$V_{CE}$ = -5V, I <sub>E</sub> =20mA, f=100MHz
Output capacitance	Cob	-	7	-	pF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0A, f=1MHz

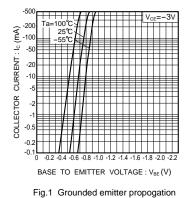
#### Packaging specifications

		Package	Taping
		Code	T146
Туре	h <sub>FE</sub>	Basic ordering unit (pieces)	3000
2SA1036K	PQR		0

#### h<sub>FE</sub> values are classifies as follows.

Item	Р	Q	R
h <sub>FE</sub>	82 to 180	120 to 270	180 to 390

#### Electrical characteristic curves



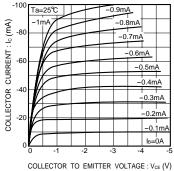




Fig.2 Grounded emitter output characteristics (I)

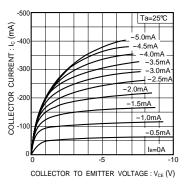


Fig.3 Ground emitter output characteristics (II)

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#### 100 1000 V<sub>CE(sal)</sub> (V) Ta=25℃ ے بے 500 ĥ COLLECTOR SATURATION VOLTAGE : -3V -0.5 N 200 .. GAIN 200 100°C Ta шù 25°C DC CURRENT CURRENT -0. 55°C 100 100 -0.1 =50 50 В 50 -0.0 10 20 20L -0.02 -5 -10 -20 -50 -100 200 1000 -5 -10 -20 -50 -100 -200 -500 -1000 -5 -10 -20 -50 -100 -200 -500 -1 -2 -2 COLLECTOR CURRENT : $I_{c}$ (mA) COLLECTOR CURRENT : $I_c$ (mA) COLLECTOR CURRENT : Ic (mA) Fig.5 DC current gain vs. Fig.6 Collector emitter saturation Fig.4 DC current gain vs. voltage vs. collector current (I) collector current (I) collector current (II) Ta=25°C V<sub>CE</sub>=-5V Ta=25℃ f=1MHz I<sub>E</sub>=0A -1.0 TRANSITION FREQUENCY : f<sub>1</sub> (MHz) 00 000 000 00 000 000 -0. -0A ++ HH 100°C Ta= 200 25°C COLLECTOR -0.02 EMITTER -0.01 0.5 5 10 20 50 2 -20 -50 -100 -200 -500 1000 0.5 -5 -10 -20 -50 -5 -10 EMITTER CURRENT : $I_E$ (mA) COLLECTOR TO BASE VOLTAGE : $V_{CB}$ (V) COLLECTOR CURRENT : I<sub>c</sub> (mA) EMITTER TO BASE VOLTAGE : VEB (V) Fig.8 Gain bandwidth product vs. Fig.7 Collector-emitter saturation Fig.9 Collectur output capacitance vs. emitter current voltage vs. collector current (II) collector-base voltage. Emitter input capacitance vs. emitter -base voltage

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